

A6  
Covell

depositing a resist over the insulating layer first regions;  
depositing a second conductive material within the insulating layer second region  
trenches;  
removing the resist;  
depositing a thin dielectric layer over the insulating layer first region within the first  
region trenches; and  
depositing a third conductive material over the thin dielectric layer within the first  
region trenches.

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12. (Amended) A method of fabricating a vertical metal-insulator-metal capacitor (MIMCap),  
comprising:

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providing a wafer having a workpiece;  
depositing an inter-level dielectric over the workpiece;  
patterning the inter-level dielectric with a plurality of trenches, the inter-level  
dielectric comprising at least one first region and at least one second region, the first region  
comprising trenches for at least one MIMCap, the second region comprising trenches for a plurality  
of conductive lines;

depositing a conductive liner over the inter-level dielectric within the trenches;  
depositing a seed layer over the conductive liner;  
depositing a resist over the seed layer;  
removing the resist over the seed layer in the inter-level dielectric second regions,  
leaving resist over the seed layer in the inter-level dielectric first regions;  
depositing a first conductive material within the inter-level dielectric second region  
trenches to form a plurality of conductive lines;  
removing the resist;  
depositing a MIMCap dielectric over the inter-level dielectric first region within the  
first region trenches; and  
depositing a second conductive material over the MIMCap dielectric within the  
first region trenches to form a MIMCap top plate.

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